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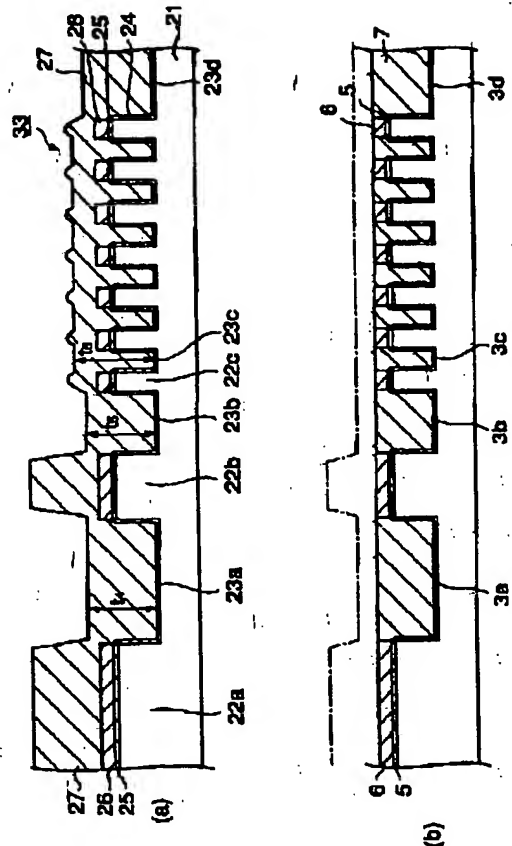
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TITLE : MANUFACTURE OF
SEMICONDUCTOR DEVICE



ABSTRACT : PROBLEM TO BE SOLVED: To improve a throughput in a step for burying an insulating film into a recessed part and keep flatness of a polished face, in a method for manufacturing a semiconductor device that includes a step for polishing an oxide insulating film with an uneven film on its surface.

SOLUTION: A manufacturing method includes a step for forming an abrasion stopping film 26 with an opening on a semiconductor substrate 21, etching the semiconductor substrate 21 through the opening to form grooves 23a to 23d, and forming an insulating film 27 in the grooves 23a to 23d and on the semiconductor substrate 21. The method further includes a step for feeding first polishing slurry on the polishing face of the insulating film 27, polishing the oxide insulating face using first polishing cloth 102 having a polishing face with first polishing hardness, feeding second polishing slurry to the polishing face of the insulating film 27, and polishing the polishing face of the oxide insulating film 27 by using second polishing cloth with second hardness lower than the first hardness until the abrasion stopping film 26 is exposed.

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